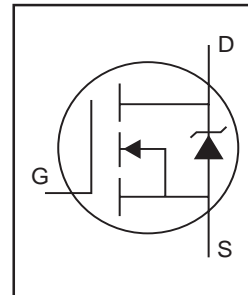


Features

- Advanced Process Technology
- Key Parameters Optimized for Class-D Audio Amplifier Applications
- Low $R_{DS(ON)}$ for Improved Efficiency
- Low Q_g and Q_{sw} for Better THD and Improved Efficiency
- Low Q_{rr} for Better THD and Lower EMI
- 175°C Operating Junction Temperature for Ruggedness
- Repetitive Avalanche Capability for Robustness and Reliability

Key Parameters		
V_{DS}	55	V
$R_{DS(ON)}$ typ. @ $V_{GS} = 10V$	42	m Ω
$R_{DS(ON)}$ typ. @ $V_{GS} = 4.5V$	57	m Ω
Q_g typ.	28	nC
T_J max	175	°C



Description

This Digital Audio HEXFET[®] is specifically designed for Class-D audio amplifier applications. This MosFET utilizes the latest processing techniques to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery and internal Gate resistance are optimized to improve key Class-D audio amplifier performance factors such as efficiency, THD and EMI. Additional features of this MosFET are 175°C operating junction temperature and repetitive avalanche capability. These features combine to make this MosFET a highly efficient, robust and reliable device for Class-D audio amplifier applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	55	V
V_{GS}	Gate-to-Source Voltage	±20	
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	19	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	13	
I_{DM}	Pulsed Drain Current ①	80	
P_D @ $T_C = 25^\circ C$	Power Dissipation	39	W
P_D @ $T_C = 100^\circ C$	Power Dissipation	20	
	Linear Derating Factor	0.26	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-40 to + 175	°C
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

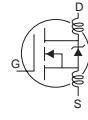
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	3.84	°C/W
$R_{\theta JA}$	Junction-to-Ambient ④	—	65	

Notes ① through ⑤ are on page 7

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

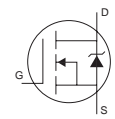
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	15	—	mV/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	42	50	m Ω	$V_{GS} = 10V, I_D = 4.7A$ ③
		—	57	65		$V_{GS} = 4.5V, I_D = 3.8A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-4.4	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	2.0	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	8.8	—	—	S	$V_{DS} = 25V, I_D = 19A$
Q_g	Total Gate Charge	—	28	42	ns	$V_{DS} = 44V$
Q_{gs}	Pre-Vth Gate-to-Source Charge	—	3.5	—		$V_{GS} = 10V$
Q_{gd}	Gate-to-Drain Charge	—	9.5	—		$I_D = 19A$
Q_{godr}	Gate Charge Overdrive	—	15	—		See Fig. 6 and 19
$t_{d(on)}$	Turn-On Delay Time	—	5.7	—		$V_{DD} = 28V, V_{GS} = 10V$ ③
t_r	Rise Time	—	19	—	$I_D = 19A$	
$t_{d(off)}$	Turn-Off Delay Time	—	23	—	ns	$R_G = 2.5\Omega$
t_f	Fall Time	—	5.3	—		
C_{iss}	Input Capacitance	—	740	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	150	—		$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	59	—		$f = 1.0\text{MHz}$, See Fig.5
C_{oss}	Effective Output Capacitance	—	250	—		$V_{GS} = 0V, V_{DS} = 0V$ to -44V
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.)
L_S	Internal Source Inductance	—	7.5	—		from package and center of die contact

**Avalanche Characteristics**

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	130	mJ
I_{AR}	Avalanche Current ⑤	See Fig. 14, 15, 17a, 17b		A
E_{AR}	Repetitive Avalanche Energy ⑤			mJ

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	19	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	110		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 19A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	52	78	ns	$T_J = 25^\circ\text{C}, I_F = 19A$
Q_{rr}	Reverse Recovery Charge	—	100	150	nC	$di/dt = 100A/\mu s$ ③



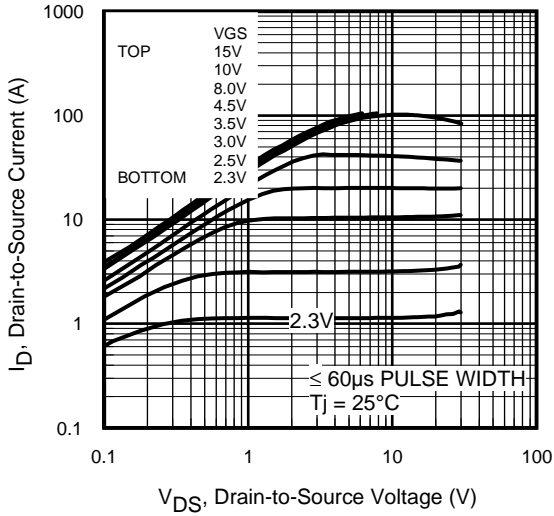


Fig 1. Typical Output Characteristics

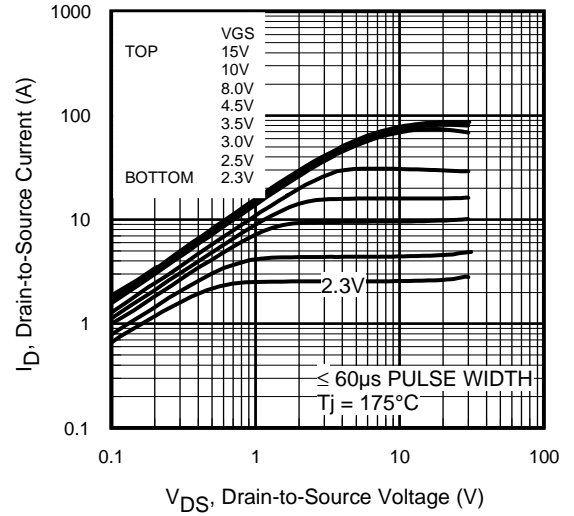


Fig 2. Typical Output Characteristics

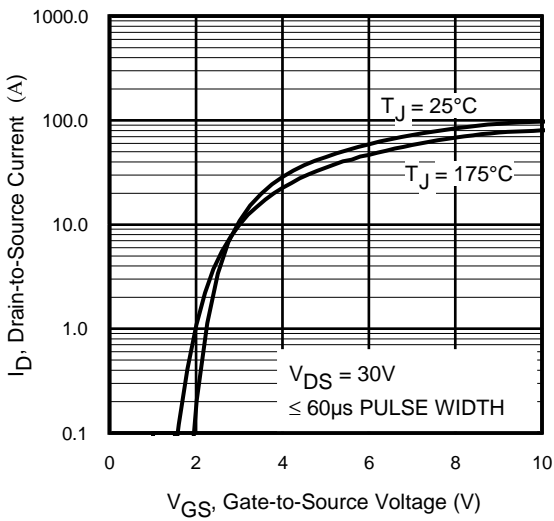


Fig 3. Typical Transfer Characteristics

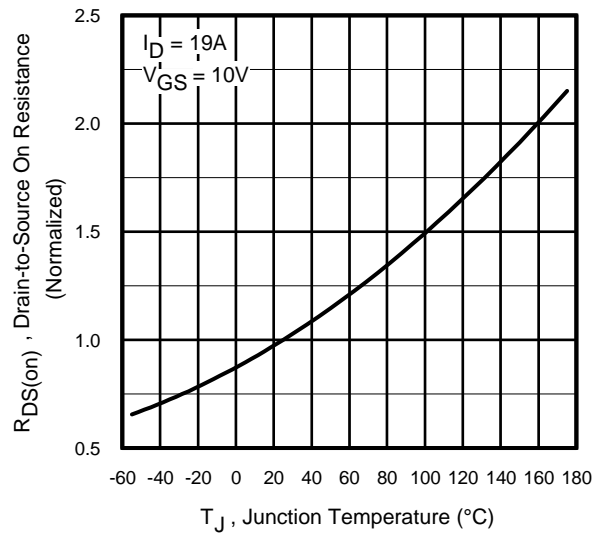


Fig 4. Normalized On-Resistance vs. Temperature

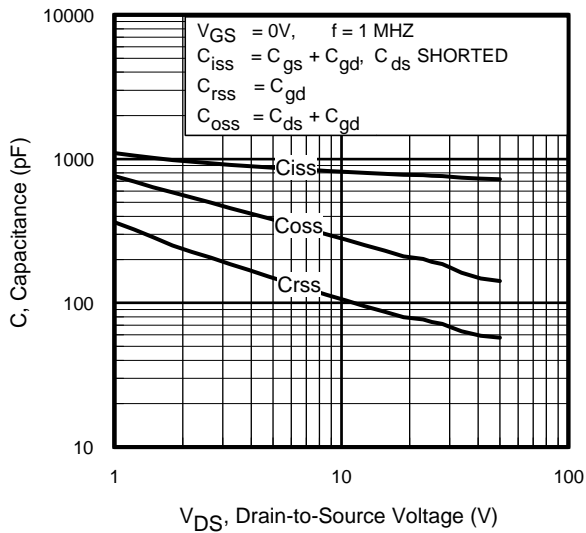


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage
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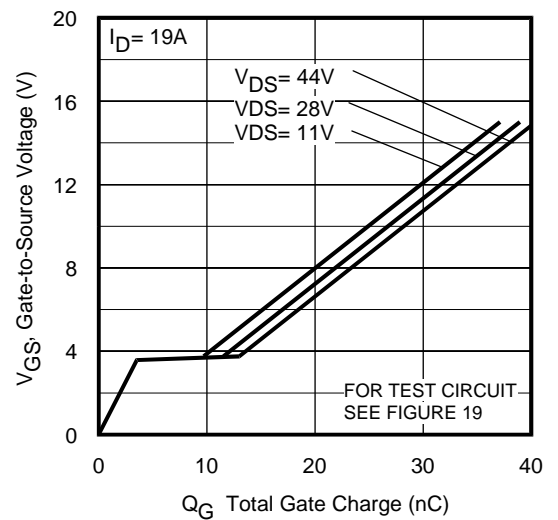


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

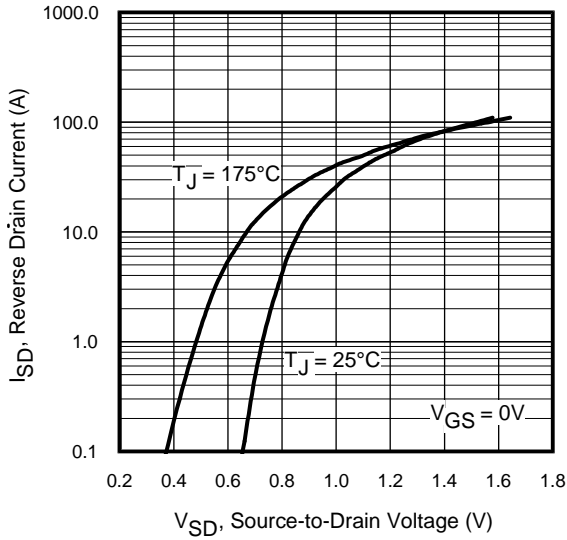


Fig 7. Typical Source-Drain Diode Forward Voltage

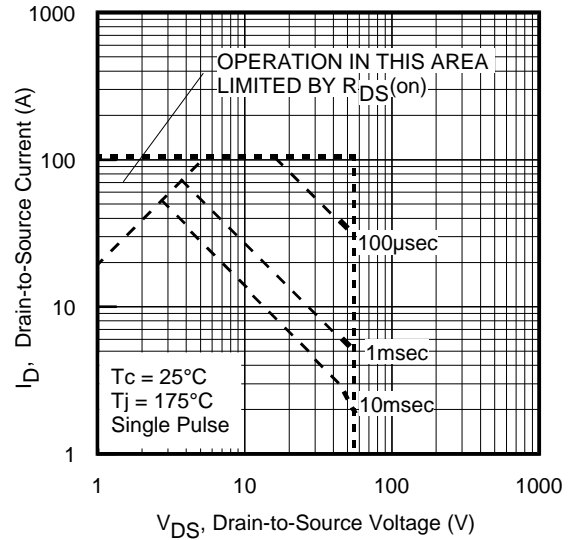


Fig 8. Maximum Safe Operating Area

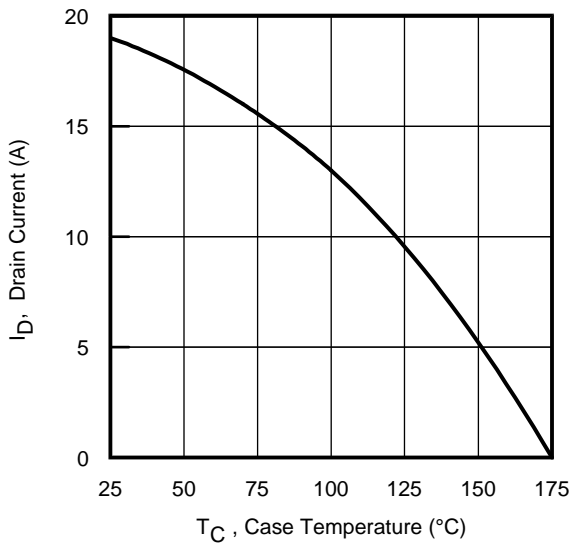


Fig 9. Maximum Drain Current vs. Case Temperature

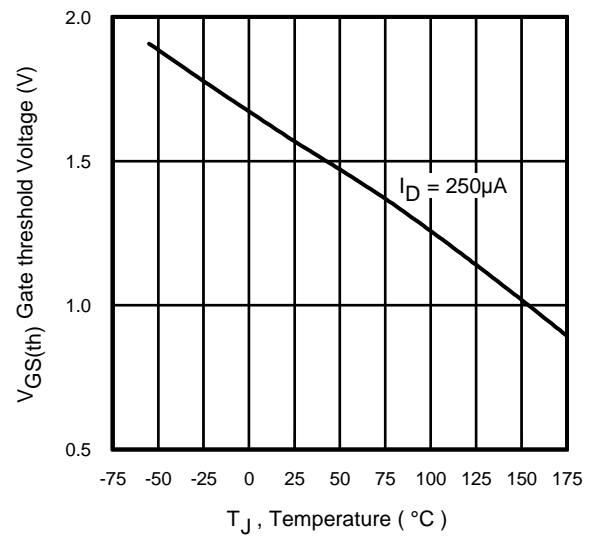


Fig 10. Threshold Voltage vs. Temperature

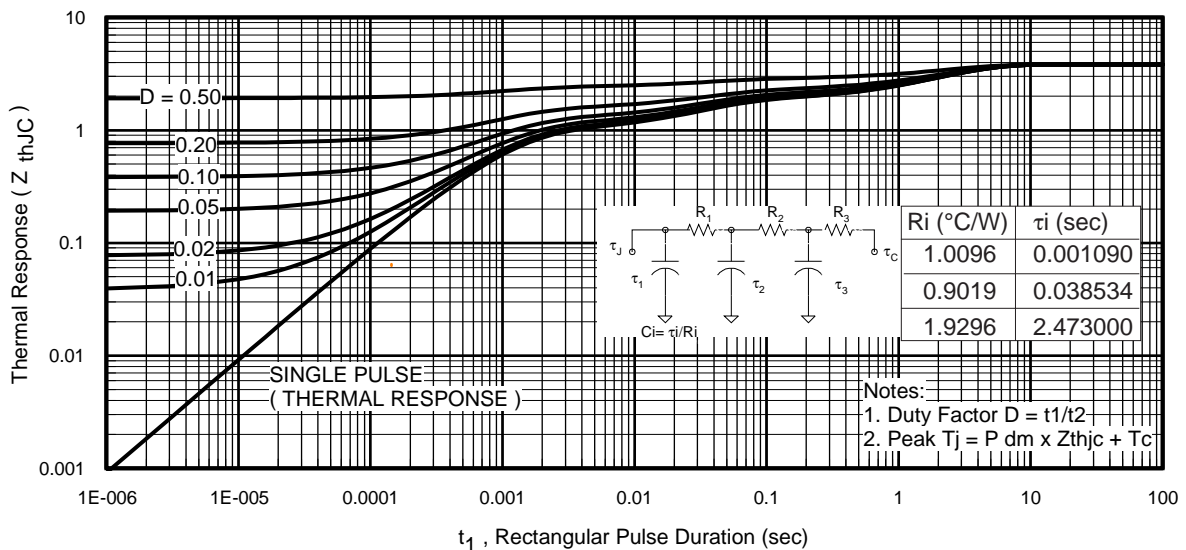


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

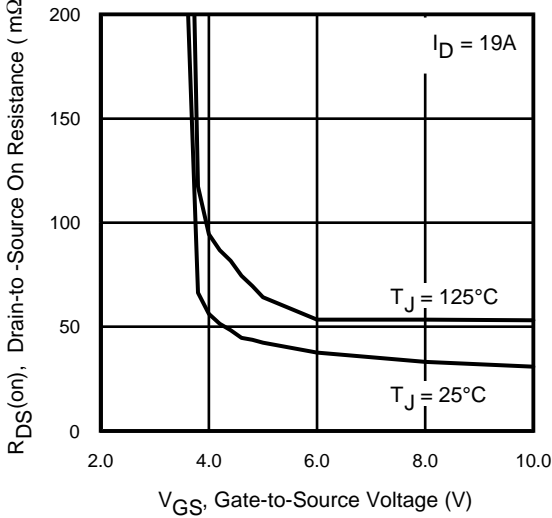


Fig 12. On-Resistance Vs. Gate Voltage

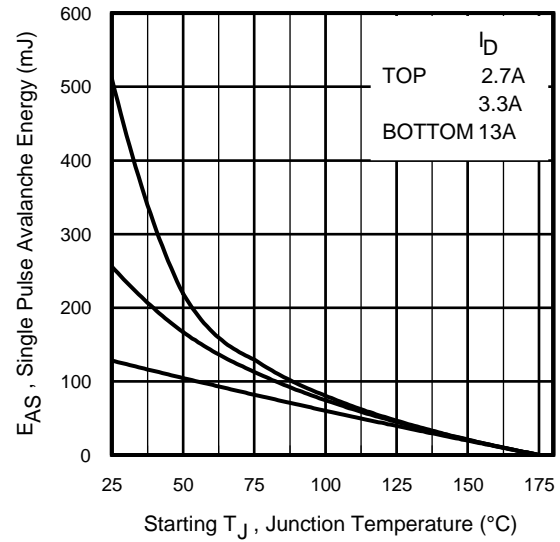


Fig 13. Maximum Avalanche Energy Vs. Drain Current

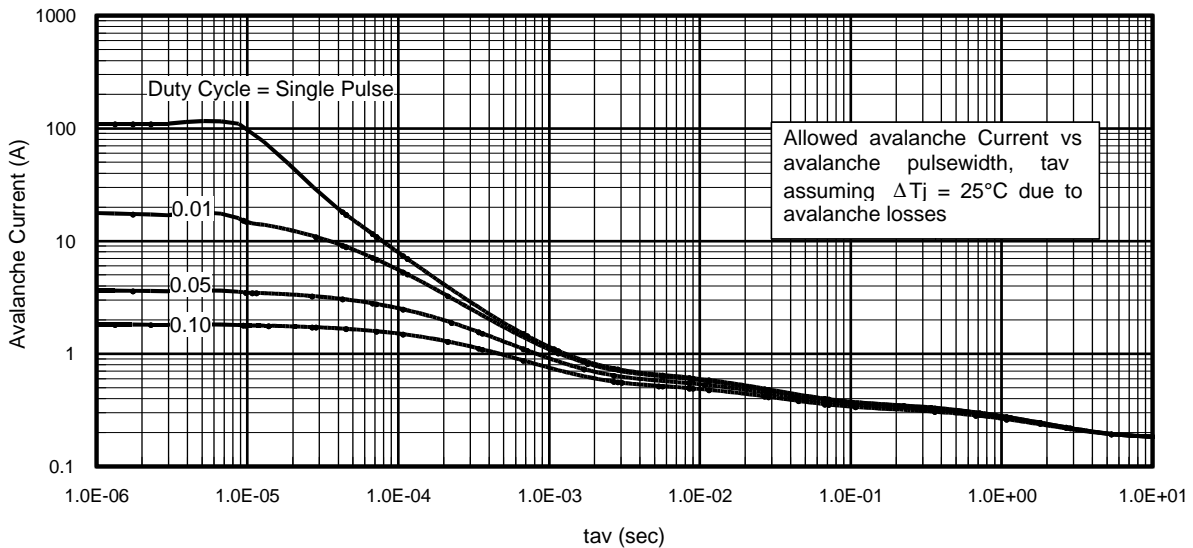


Fig 14. Typical Avalanche Current Vs. Pulsewidth

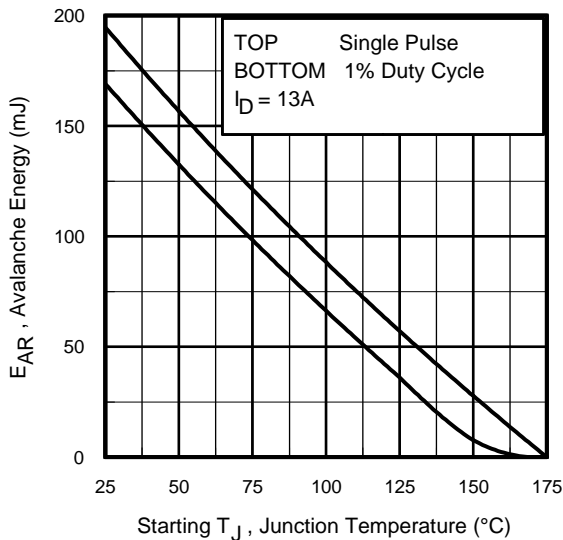


Fig 15. Maximum Avalanche Energy Vs. Temperature
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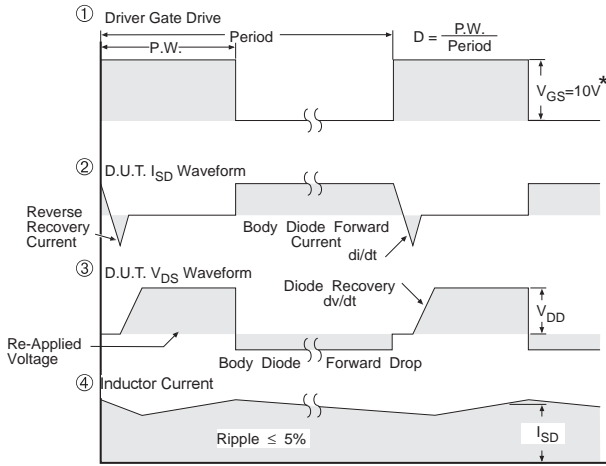
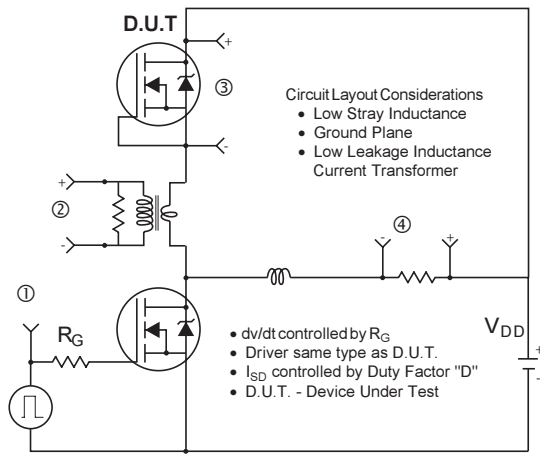
Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 17a, 17b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



* $V_{GS} = 5V$ for Logic Level Devices

Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

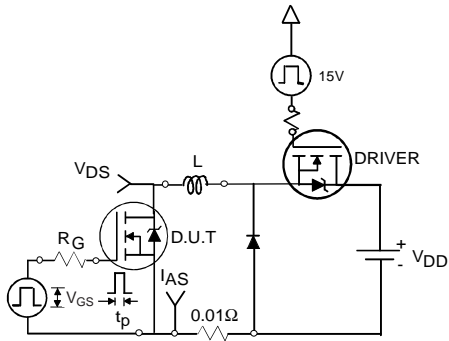


Fig 17a. Unclamped Inductive Test Circuit

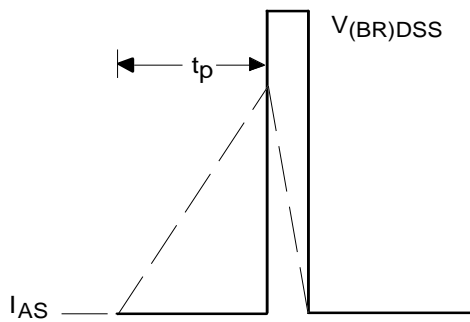


Fig 17b. Unclamped Inductive Waveforms

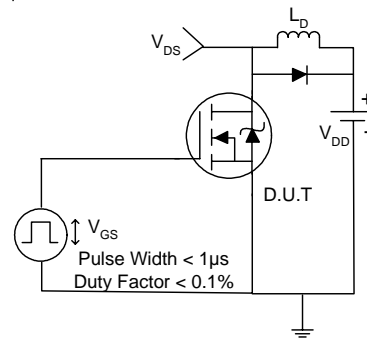


Fig 18a. Switching Time Test Circuit

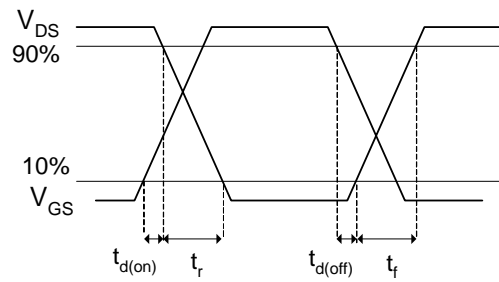


Fig 18b. Switching Time Waveforms

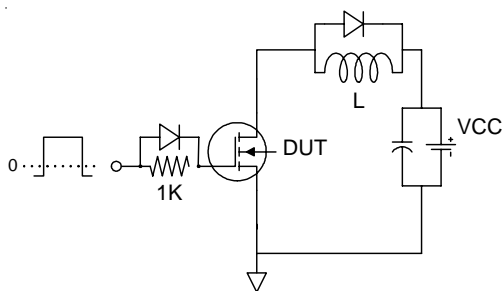


Fig 19a. Gate Charge Test Circuit

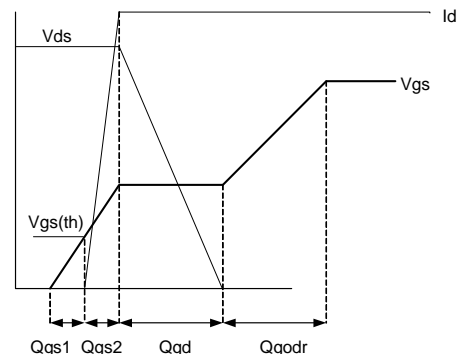


Fig 19b Gate Charge Waveform

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>